2SB0788 (2SB788)

Silicon PNP epitaxial planar type

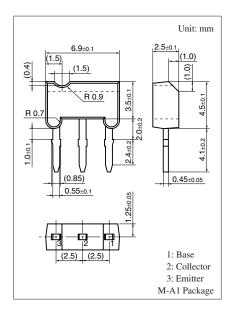
For high breakdown voltage low-noise amplification Complementary to 2SD0958 (2SD958)

Features

- \bullet High collector-emitter voltage (Base open) $V_{\mbox{CEO}}$
- Low noise voltage NV
- M type package allowing easy automatic and manual insertion as well as stand-alone fixing to the printed circuit board.

Absolute Maximum Ratings $T_a = 25^{\circ}C$

| Parameter | Symbol | Rating | Unit | | | |
|---------------------------------------|------------------|-------------|------|--|--|--|
| Collector-base voltage (Emitter open) | V _{CBO} | -120 | V | | | |
| Collector-emitter voltage (Base open) | V _{CEO} | -120 | V | | | |
| Emitter-base voltage (Collector open) | V _{EBO} | -7 | V | | | |
| Collector current | I _C | -20 | mA | | | |
| Peak collector current | I _{CP} | -50 | mA | | | |
| Collector power dissipation | P _C | 400 | mW | | | |
| Junction temperature | Tj | 150 | °C | | | |
| Storage temperature | T _{stg} | -55 to +150 | °C | | | |



Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

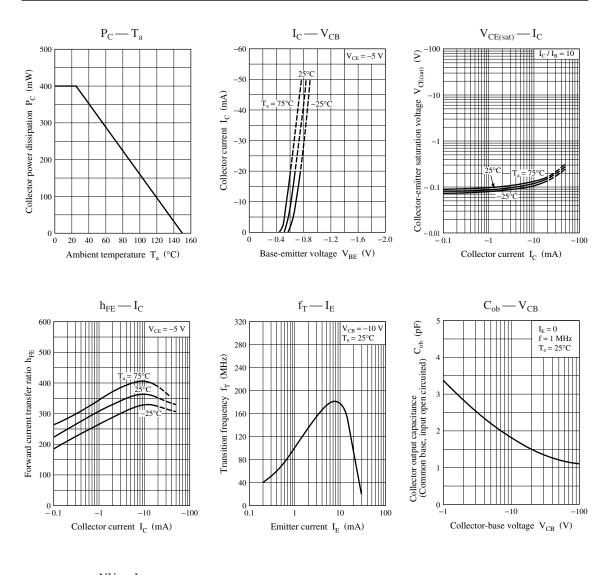
| Parameter | Symbol | Conditions | Min | Тур | Max | Unit |
|--|----------------------|--|------|-----|-------|------|
| Collector-base voltage (Emitter open) | V _{CBO} | $I_{C} = -10 \ \mu A, I_{E} = 0$ | -120 | | | V |
| Collector-emitter voltage (Base open) | V _{CEO} | $I_{\rm C} = -1 {\rm mA}, I_{\rm B} = 0$ | -120 | | | V |
| Emitter-base voltage (Collector open) | V _{EBO} | $I_E = -10 \ \mu A, \ I_C = 0$ | -7 | | | V |
| Collector-base cutoff current (Emitter open) | I _{CBO} | $V_{CB} = -50 \text{ V}, I_E = 0$ | | | -100 | nA |
| Collector-emitter cutoff current (Base open) | I _{CEO} | $V_{CE} = -50 \text{ V}, I_B = 0$ | | | -1 | μΑ |
| Forward current transfer ratio * | h _{FE} | $V_{CE} = -2 V, I_C = -2 A$ | 180 | | 520 | _ |
| Collector-emitter saturation voltage | V _{CE(sat)} | $I_{\rm C} = -20$ mA, $I_{\rm B} = -2$ mA | | | - 0.6 | V |
| Noise voltage | NV | $V_{CE} = -40 \text{ V}, I_C = -1 \text{ mA}, G_V = 80 \text{ dB}$ | | | 150 | mV |
| | | $R_g = 100 \text{ k}\Omega$, Function = FLAT | | | | |

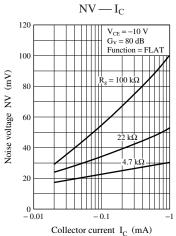
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors. 2. *: Rank classification

| Rank | Q | R |
|-----------------|------------|------------|
| h _{FE} | 180 to 360 | 260 to 520 |

Note) The part number in the parenthesis shows conventional part number.

Panasonic





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